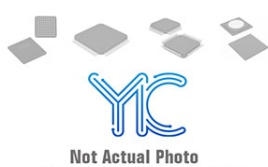


Spezifikationen	
Artikelnummer	TPH3R704PL,L1Q
Hersteller	Toshiba Semiconductor and Storage
Beschreibung	MOSFET N-CH 40V 92A TSON
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	2511 pcs Stock
VGS (th) (Max) @ Id	2.4V @ 0.2mA
Vgs (Max)	±20V
Technologie	MOSFET (Metal Oxide)
Supplier Device-Gehäuse	8-SOP Advance (5x5)
Serie	U-MOSIX-H
Rds On (Max) @ Id, Vgs	3.7 mOhm @ 46A, 10V
Verlustleistung (max)	960mW (Ta), 81W (Tc)
Verpackung	Tape & Reel (TR)
Verpackung / Gehäuse	8-PowerVDFN
Betriebstemperatur	175°C
Befestigungsart	Surface Mount
Eingabekapazität (Ciss) (Max) @ Vds	2500pF @ 20V
Gate Charge (Qg) (Max) @ Vgs	27nC @ 10V
Typ FET	N-Channel
FET-Merkmal	-
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Drain-Source-Spannung (Vdss)	40V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	92A (Tc)

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TPH3R203NL, L1Q
Toshiba Semiconductor and Storage
MOSFET N-CH 30V 47A 8-SOP

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